

HT-02-026



November 18, 2003

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/647,718 08/25/03

Yimin Guo

MAGNETIC MEMORY WITH SELF-ALIGNED
MAGNETIC KEEPER STRUCTURE

Grp. Art Unit:

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.


The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on November 21, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 11/21/03


U.S. Patent Application Publication US 2002/0055190 A1 to Anthony, "Magnetic Memory With Structures that Prevent Disruptions to Magnetization in Sense Layer," provides a keeper structure which is a soft magnetic material surrounding a current carrying conductor beneath the sense layer.

U.S. Patent 6,358,757 to Anthony, "Method for Forming Magnetic Memory With Structures that Prevent Disruptions to Magnetization in Sense Layers," provides a method for forming an array of MRAM devices at the intersections of orthogonally crossing upper and lower conductors in which the lower conductors are surrounded by soft magnetic keeper layers.

U.S. Patent 6,413,788 to Tuttle, "Keepers for MRAM Electrodes," within a variety of embodiments, teaches methods for forming keeper structures around both upper and lower conductors in damascene type trench configurations.

U.S. Patent 6,417,561 to Tuttle, "Keepers for MRAM Electrodes," discloses a magnetic memory device and method wherein a bit region sensitive to magnetic fields and preferably comprising a tunneling magnetoresistance (TMR) structure is located between a top electrode with a magnetic keeper and a bottom electrode with a magnetic keeper.

Sincerely,


Stephen B. Ackerman, Reg. #37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Docet Number (Optional)

HT-02-026

Application Number

10/647,718

Applicants:

Yimin Guo

Filing Date

08/25/03

Group Art Unit

U. S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		U.S. Patent Application Publication US 2002/0055190 A1
		to Anthony, "Magnetic Memory with Structures
		that Prevent Disruptions to Magnetization in Sense
		Layer", Pub Date 5/9/02, US Class 438/3.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.